

**COMPLEMENTARY PAIR SMALL SIGNAL TRANSISTOR IN SOT363**

## Features

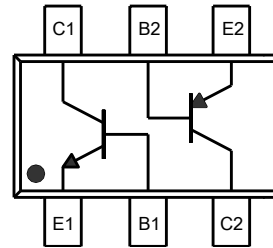
- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([BC847PNQ](#))**

## Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.006 grams (Approximate)



Top View



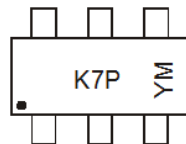
Device Schematic  
Top View

## Ordering Information (Note 4)

| Part Number  | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity per Reel |
|--------------|------------|---------|--------------------|-----------------|-------------------|
| BC847PN-7-F  | AEC-Q101   | K7P     | 7                  | 8               | 3,000             |
| BC847PN-13-F | AEC-Q101   | K7P     | 13                 | 8               | 10,000            |
| BC847PN-7R-F | AEC-Q101   | K7P     | 7                  | 8               | 3,000             |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



K7P = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: D = 2016)  
 M = Month (ex: 9 = September)

### Date Code Key

| Year | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 |
|------|------|------|------|------|------|------|------|------|
| Code | C    | D    | E    | F    | G    | H    | I    | J    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Absolute Maximum Ratings: NPN, BC847B Type (Q<sub>1</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic            | Symbol           | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage    | V <sub>CB0</sub> | 50    | V    |
| Collector-Emitter Voltage | V <sub>CEO</sub> | 45    | V    |
| Emitter-Base Voltage      | V <sub>EBO</sub> | 6     | V    |
| Collector Current         | I <sub>C</sub>   | 100   | mA   |
| Peak Collector Current    | I <sub>CM</sub>  | 200   | mA   |
| Peak Emitter Current      | I <sub>EM</sub>  | 200   | mA   |

**Absolute Maximum Ratings: PNP, BC857B Type (Q<sub>2</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic            | Symbol           | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage    | V <sub>CB0</sub> | -50   | V    |
| Collector-Emitter Voltage | V <sub>CEO</sub> | -45   | V    |
| Emitter-Base Voltage      | V <sub>EBO</sub> | -6    | V    |
| Collector Current         | I <sub>C</sub>   | -100  | mA   |
| Peak Collector Current    | I <sub>CM</sub>  | -200  | mA   |
| Peak Emitter Current      | I <sub>EM</sub>  | -200  | mA   |

**Thermal Characteristics – Total Device** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                                   | Symbol                            | Value       | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 5) Total Device          | P <sub>D</sub>                    | 200         | mW   |
| Thermal Resistance, Junction to Ambient (Note 5) | R <sub>θJA</sub>                  | 625         | °C/W |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -65 to +150 | °C   |

Note: 5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR-4 PCB; the device is measured under still air conditions whilst operating in a steady-state.

**Thermal Characteristics – Total Device**

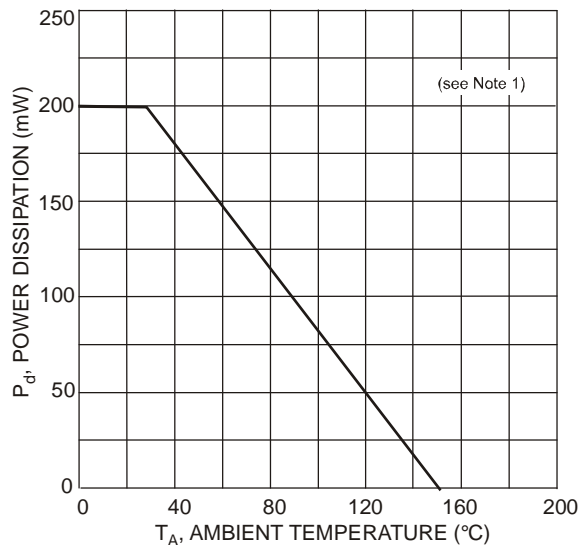


Fig. 1, Power Derating Curve (Total Device)

**Electrical Characteristics: NPN, BC847B Type (Q<sub>1</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic (Note 6)              | Symbol               | Min      | Typ        | Max        | Unit     | Test Condition   |
|--------------------------------------|----------------------|----------|------------|------------|----------|--|
| Collector-Base Breakdown Voltage     | BV <sub>CB0</sub>    | 50       | —          | —          | V        | I <sub>C</sub> = 100μA   |
| Collector-Emitter Breakdown Voltage  | BV <sub>CEO</sub>    | 45       | —          | —          | V        | I <sub>C</sub> = 10mA  |
| Emitter-Base Breakdown Voltage       | BV <sub>EBO</sub>    | 6        | —          | —          | V        | I <sub>E</sub> = 100μA   |
| DC Current Gain                      | h <sub>FE</sub>      | 200      | 290        | 450        | —        | V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA   |
| Collector-Emitter Saturation Voltage | V <sub>CE(SAT)</sub> | —        | 90<br>200  | 250<br>600 | mV       | I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA<br>I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA    |
| Base-Emitter Saturation Voltage      | V <sub>BE(SAT)</sub> | —        | 700<br>900 | —          | mV       | I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA<br>I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA    |
| Base-Emitter Voltage                 | V <sub>BE(ON)</sub>  | 580<br>— | 660<br>—   | 700<br>720 | mV       | V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA<br>V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA    |
| Collector-Cutoff Current             | I <sub>CB0</sub>     | —<br>—   | —<br>—     | 15<br>5.0  | nA<br>μA | V <sub>CB</sub> = 30V<br>V <sub>CB</sub> = 30V, T <sub>A</sub> = +150°C                            |
| Gain Bandwidth Product               | f <sub>T</sub>       | 100      | 300        | —          | MHz      | V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA,<br>f = 100MHz                                       |
| Collector-Base Capacitance           | C <sub>CB0</sub>     | —        | 3.5        | 6.0        | pF       | V <sub>CB</sub> = 10V, f = 1.0MHz  |
| Noise Figure                         | NF                   | —        | 2.0        | 10         | dB       | V <sub>CE</sub> = 5V, I <sub>C</sub> = 200μA,<br>R <sub>g</sub> = 2.0kΩ, f = 1.0kHz,<br>Δf = 200Hz |

Note: 6. Short duration pulse test used to minimize self-heating effect.

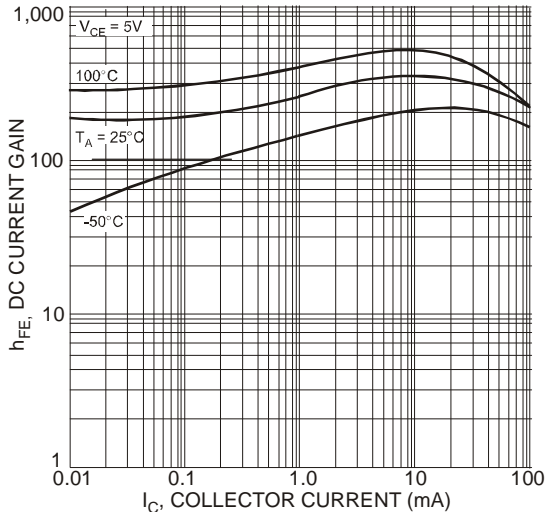


Figure 2. Typical DC Current Gain vs. Collector Current (BC847B Type)

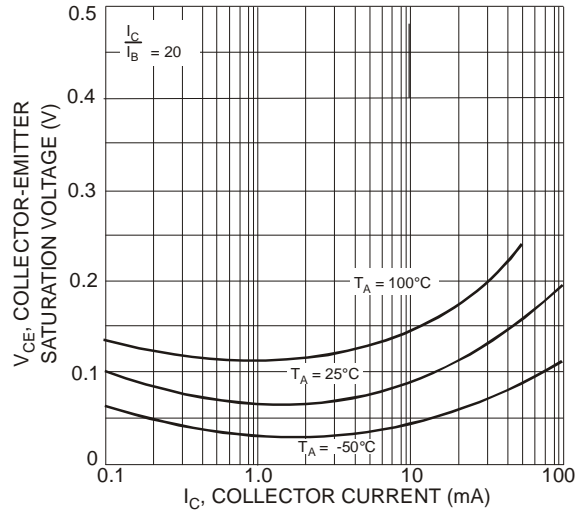


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC847B Type)

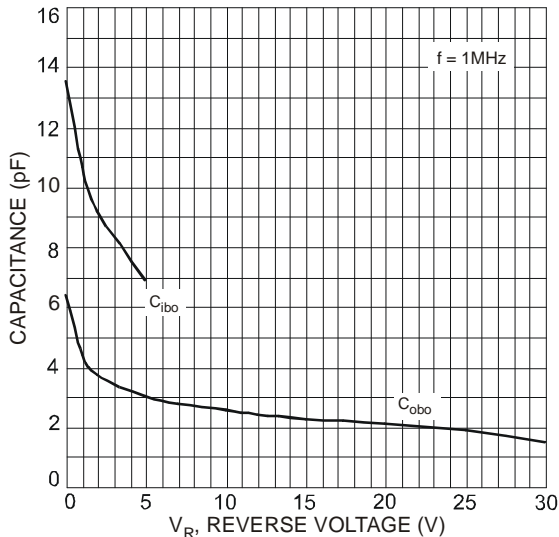


Figure 4. Typical Capacitance Characteristics (BC847B Type)

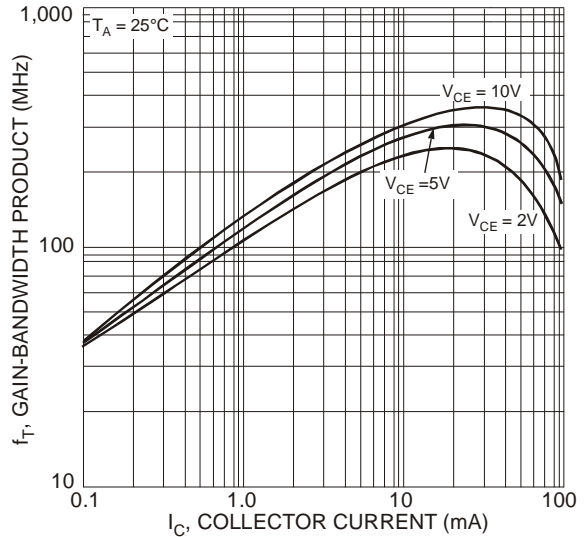


Figure 5. Typical Gain-Bandwidth Product vs. Collector Current (BC847B Type)

**Electrical Characteristics: PNP, BC857B Type (Q<sub>2</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic (Note 7)              | Symbol               | Min  | Typ          | Max          | Unit     | Test Condition   |
|--------------------------------------|----------------------|------|--------------|--------------|----------|--|
| Collector-Base Breakdown Voltage     | BV <sub>CBO</sub>    | -50  | —            | —            | V        | I <sub>C</sub> = -100μA  |
| Collector-Emitter Breakdown Voltage  | BV <sub>CEO</sub>    | -45  | —            | —            | V        | I <sub>C</sub> = -10mA   |
| Emitter-Base Breakdown Voltage       | BV <sub>EBO</sub>    | -6   | —            | —            | V        | I <sub>E</sub> = -100μA  |
| DC Current Gain                      | h <sub>FE</sub>      | 220  | 290          | 475          | —        | V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA   |
| Collector-Emitter Saturation Voltage | V <sub>CE(SAT)</sub> | —    | -75<br>-250  | -300<br>-650 | mV       | I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA<br>I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA  |
| Base-Emitter Saturation Voltage      | V <sub>BE(SAT)</sub> | —    | -700<br>-850 | —<br>-950    | mV       | I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA<br>I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA  |
| Base-Emitter Voltage                 | V <sub>BE(ON)</sub>  | -600 | -650         | -750<br>-820 | mV       | V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA<br>V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA  |
| Collector-Cutoff Current             | I <sub>CBO</sub>     | —    | —            | -15<br>-4.0  | nA<br>μA | V <sub>CB</sub> = -30V<br>V <sub>CB</sub> = -30V, T <sub>A</sub> = +150°C                            |
| Gain Bandwidth Product               | f <sub>T</sub>       | 100  | 200          | —            | MHz      | V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA,<br>f = 100MHz                                       |
| Collector-Base Capacitance           | C <sub>CBO</sub>     | —    | 3            | 4.5          | pF       | V <sub>CB</sub> = -10V, f = 1.0MHz   |
| Noise Figure                         | NF                   | —    | —            | 10           | dB       | V <sub>CE</sub> = -5V, I <sub>C</sub> = -200μA,<br>R <sub>g</sub> = 2.0kΩ, f = 1.0kHz,<br>Δf = 200Hz |

Note: 7. Short duration pulse test used to minimize self-heating effect.

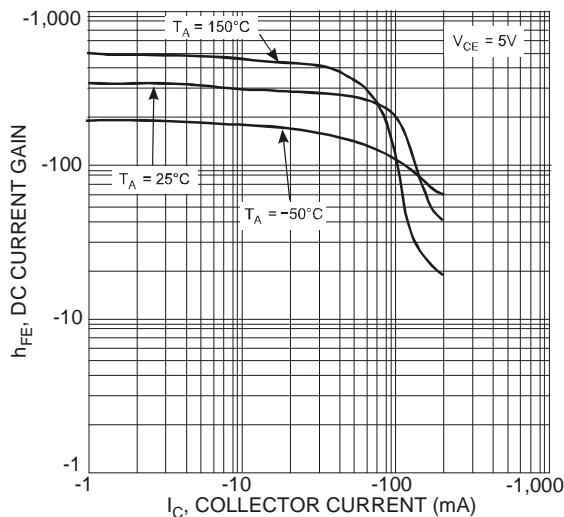


Figure 6. Typical DC Current Gain vs. Collector Current (BC857B Type)

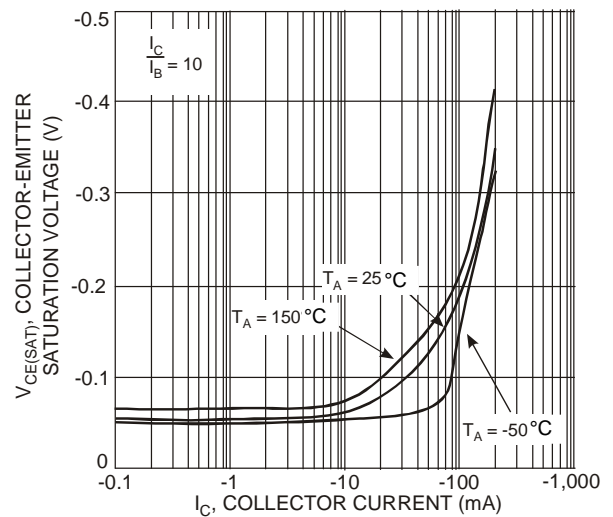


Figure 7. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC857B Type)

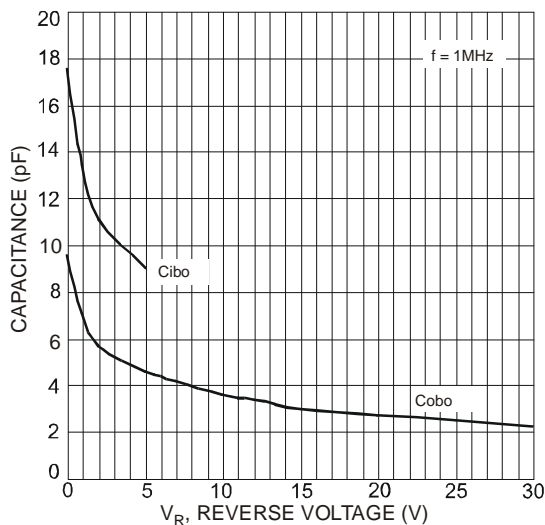


Figure 8. Typical Capacitance Characteristics (BC857B Type)

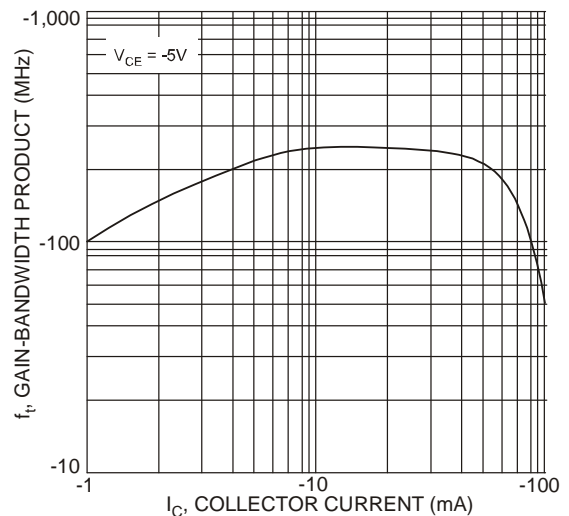
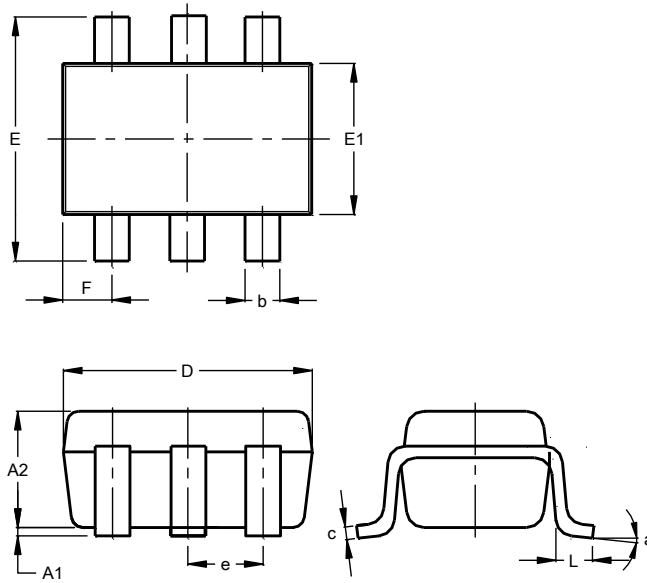


Figure 9. Typical Gain-Bandwidth Product vs. Collector Current (BC857B Type)

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**

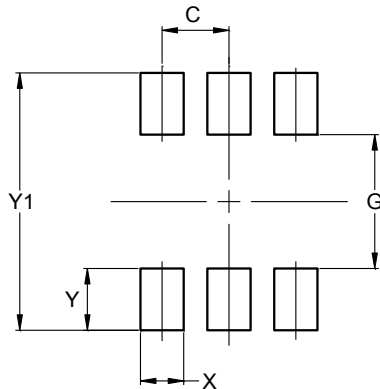


| SOT363               |           |      |       |
|----------------------|-----------|------|-------|
| Dim                  | Min       | Max  | Typ   |
| A1                   | 0.00      | 0.10 | 0.05  |
| A2                   | 0.90      | 1.00 | 1.00  |
| b                    | 0.10      | 0.30 | 0.25  |
| c                    | 0.10      | 0.22 | 0.11  |
| D                    | 1.80      | 2.20 | 2.15  |
| E                    | 2.00      | 2.20 | 2.10  |
| E1                   | 1.15      | 1.35 | 1.30  |
| e                    | 0.650 BSC |      |       |
| F                    | 0.40      | 0.45 | 0.425 |
| L                    | 0.25      | 0.40 | 0.30  |
| a                    | 0°        | 8°   | --    |
| All Dimensions in mm |           |      |       |

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.650         |
| G          | 1.300         |
| X          | 0.420         |
| Y          | 0.600         |
| Y1         | 2.500         |

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